

# PZTA42T1G

## High Voltage Transistor Surface Mount

### NPN Silicon

#### Features

- PZTA42T1G is Complement to PZTA92T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Open Base)	$V_{CEO}$	300	Vdc
Collector-Base Voltage (Open Emitter)	$V_{CBO}$	300	Vdc
Emitter-Base Voltage (Open Collector)	$V_{EBO}$	6.0	Vdc
Collector Current (DC)	$I_C$	500	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	1.5	W
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board  
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

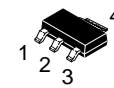
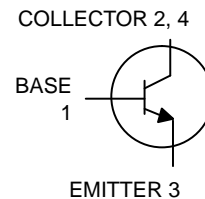
2. Device mounted on a FR-4 glass epoxy printed circuit board  
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.



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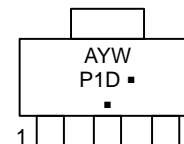
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### SOT-223 PACKAGE NPN SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT



SOT-223  
CASE 318E  
STYLE 1

#### MARKING DIAGRAM



P1D = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
PZTA42T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZTA42T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# PZTA42T1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (Note 3) ( $I_C = 1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	300	–	Vdc
Collector-Base Breakdown Voltage ( $I_C = 100\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	300	–	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 100\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Collector-Base Cutoff Current ( $V_{CB} = 200\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	0.1	$\mu\text{A}$
Emitter-Base Cutoff Current ( $V_{BE} = 6.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	0.1	$\mu\text{A}$

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 30\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ )	$h_{FE}$	25 40 40	– – –	–
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## DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	50	–	MHz
Feedback Capacitance ( $V_{CB} = 20\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{re}$	–	3.0	pF
Collector-Emitter Saturation Voltage ( $I_C = 20\text{ mA}$ , $I_B = 2.0\text{ mA}$ )	$V_{CE(sat)}$	–	0.5	Vdc
Base-Emitter Saturation Voltage ( $I_C = 20\text{ mA}$ , $I_B = 2.0\text{ mA}$ )	$V_{BE(sat)}$	–	0.9	Vdc

3. Pulse Test Conditions,  $t_p = 300\text{ }\mu\text{s}$ ,  $\delta = 0.02$ .

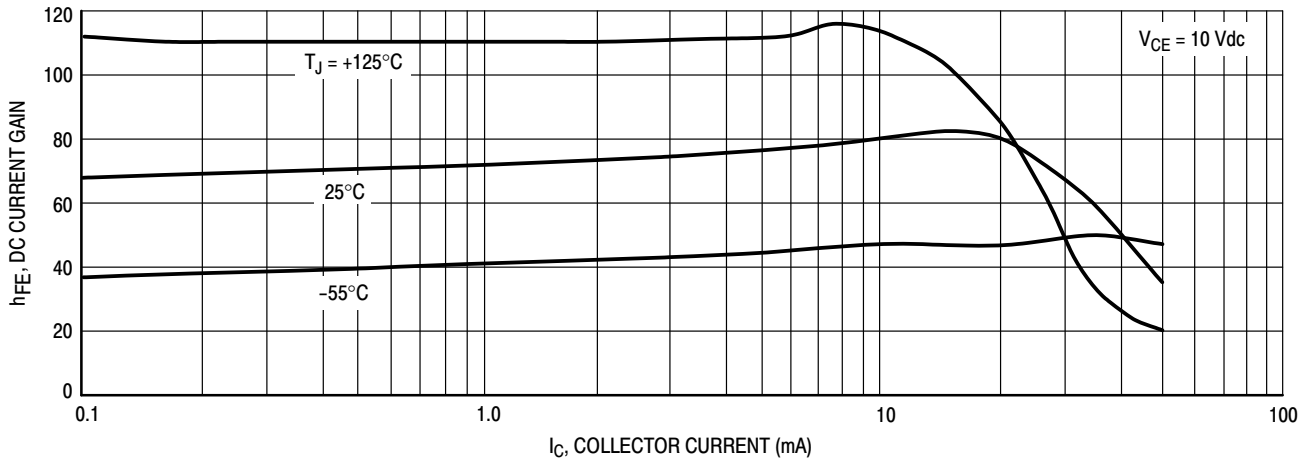


Figure 1. DC Current Gain

# PZTA42T1G

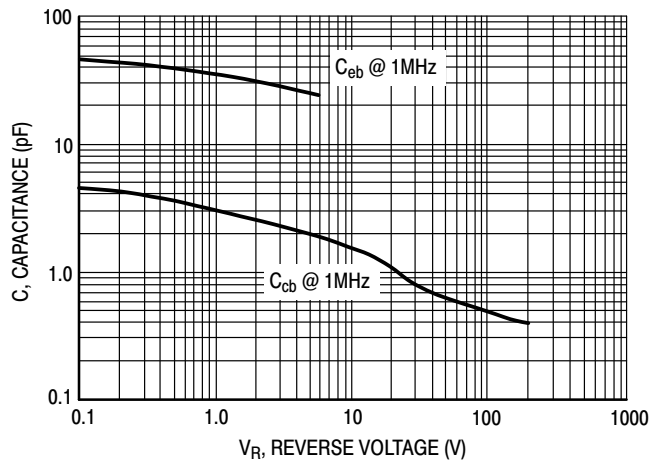


Figure 2. Capacitance

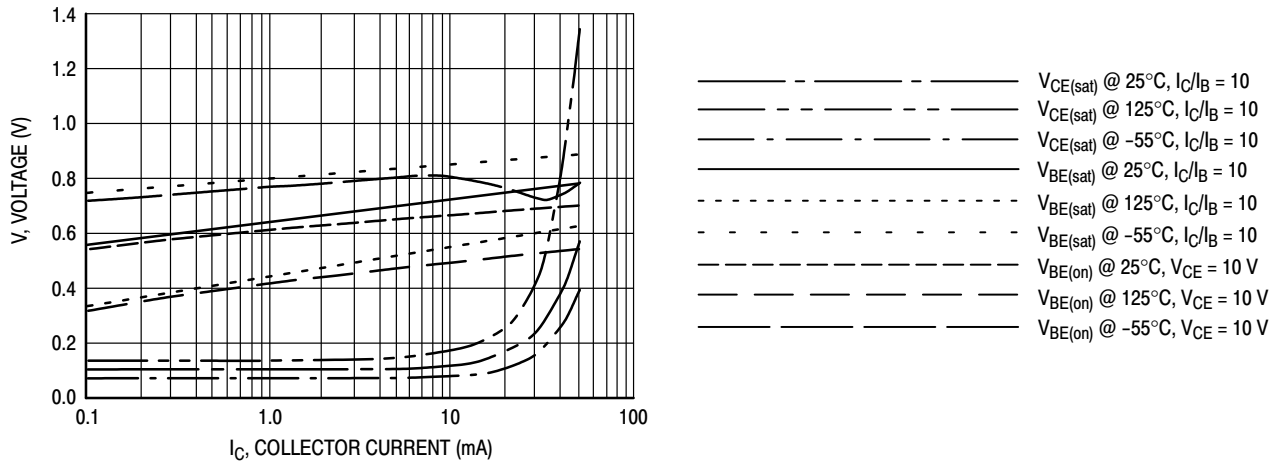


Figure 3. "ON" Voltages

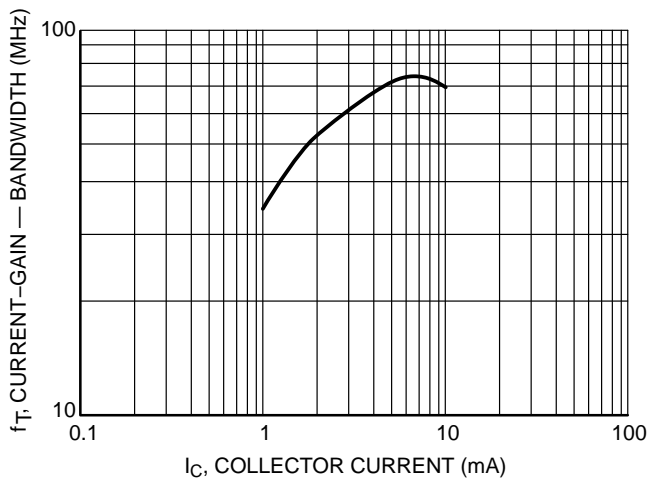


Figure 4. Current Gain Bandwidth Product

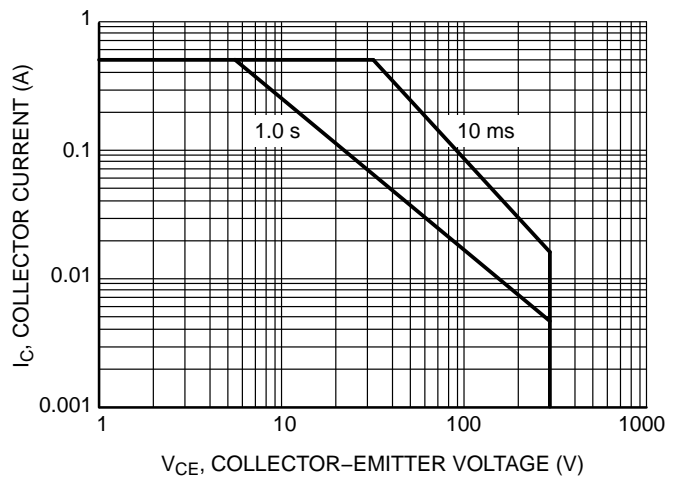


Figure 5. Safe Operating Area

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

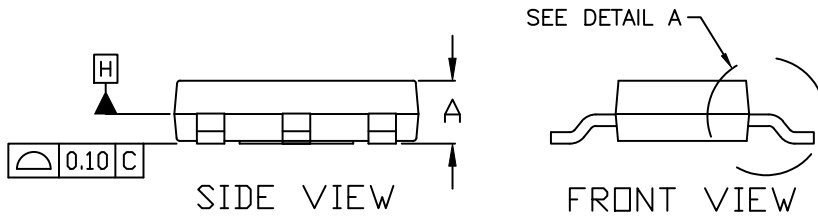
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SCALE 1:1

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

- |  |   |   |   |   |
|--|---|---|---|---|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. NC<br>4. CATHODE        | <b>STYLE 3:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN           | <b>STYLE 4:</b><br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE<br>4. DRAIN   | <b>STYLE 5:</b><br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE<br>4. GATE    |
| <b>STYLE 6:</b><br>PIN 1. RETURN<br>2. INPUT<br>3. OUTPUT<br>4. INPUT        | <b>STYLE 7:</b><br>PIN 1. ANODE 1<br>2. CATHODE<br>3. ANODE 2<br>4. CATHODE | <b>STYLE 8:</b><br>CANCELLED  | <b>STYLE 9:</b><br>PIN 1. INPUT<br>2. GROUND<br>3. LOGIC<br>4. GROUND | <b>STYLE 10:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE |
| <b>STYLE 11:</b><br>PIN 1. MT 1<br>2. MT 2<br>3. GATE<br>4. MT 2             | <b>STYLE 12:</b><br>PIN 1. INPUT<br>2. OUTPUT<br>3. NC<br>4. OUTPUT         | <b>STYLE 13:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR |   |   |


**GENERIC  
 MARKING DIAGRAM\***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)  
 \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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